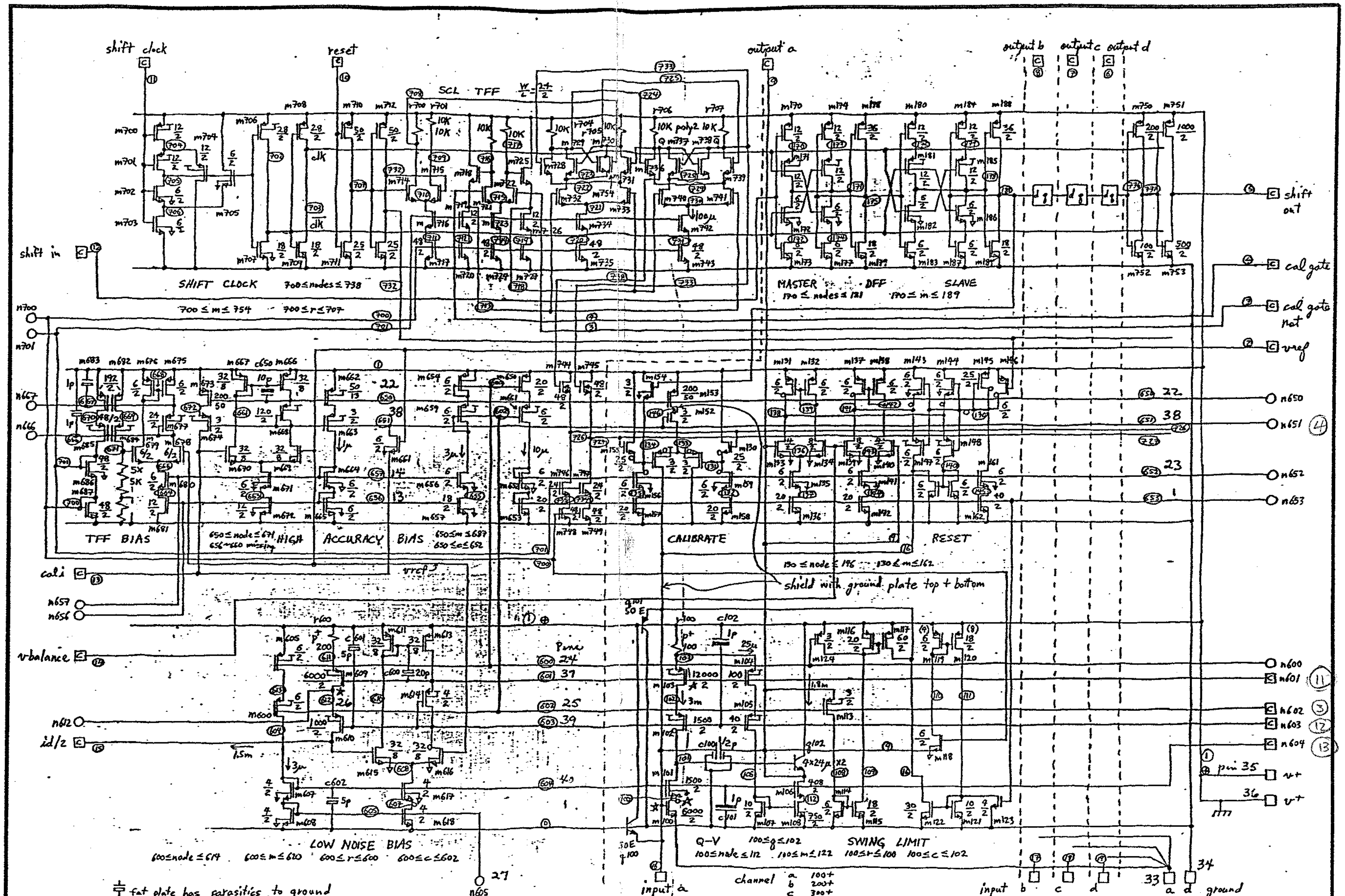

╤ fat plate has parasitics to ground
☆ low noise, low parasitic resistance
o low capacitance
[c] diode clamps on these pads

Orbit/MOSIS process, 3μ, 2 poly, 2 metal
p well, N igfet
n wafer to V+, all p igfet bulk to V+, all n igfet to gnd, unless noted
$\frac{W}{L} = \frac{25\mu}{?}$ is a flag to use a donut gate igfet with small capacitance drain
all nodes have 2nd metal dot, for probing, unless noted

M	63·4+118 = 370
Q	6
I	4(7)+16+1 = 30
P/ch	6·0.030/4 = 45mW

CHG. LTR | DRAWN BY | CHECKED BY | DATE | CHANGES

DIST I: II: III:

SHWN ON | ACCT. & SER. | DATE ISSUED | NO. REQD. | DATE REQD. | DEL. TO

DRWN. BY | DATE
CHKD. BY | SCALE
APPR. 15 May '90
ENG. Michael Wright

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Rev. D